

* Up to 4% more of extra power generated at STC

CBM4M

High Efficiency Bifacial N-type Monocrystalline Silicon Solar Cell, optimized for Glass-White Backsheet applications

Production Technology and Properties

The new photovoltaic frontier is called **BiSoN**, the **bifacial** high efficiency N-type monocrystalline silicon solar cell up to **20,7%** front efficiency, developed in collaboration with the **ISC Konstanz** R&D Institute (Germany). The **CBM3-M** Solar Cell is optimized for glass-white backsheet applications and it is able to generate extra power up to 4% (measured at STC during flash testing phase).

Bifacial Made with bifacial technology

High Efficiency 20,7% front efficiency



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Compatible with Standard Modules Machineries 100% compatible with common module assembly lines

Internal Reflection Contribution Up to 4% of extra power measured on the module during flash test phase (at STC)

N-Type N-type monocrystalline silicon solar cell

Low Insolation

Excellent performance at low insolation due to the high shunt resistance, measured on each cell

Fill Factor

High Fill Factor and low series resistance to reduce the cell to module losses

Production and quality control

• 100% Quality control of the wafers used in production, performed at each step of the production process, from

REV 01_16

raw wafer acceptance test to the electrical testing of the cell.

- Use of a MES System for total control, traceability and production improvement.
- Soft handling production to reduce the microcrack generation, breakage rate and mechanical stress.
- Innovative integrated treatment system with zero discharge capable to recover 97% of the waste process water.

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LID near zero It doesn't suffer LID-effect (Light Induced Degradation)

that is near 0% instead of 2-3% occurring to all p-type cells

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Hot Spot Protect

100% measurement of insulation resistance in dark condition to prevent the Hot Spot



Fraunhofer ISE Cells calibrated by Fraunhofer ISE



Electrical Performance Stable Electrical performance over time

-0/-0.025 With guaranteed -0/+0,025W positive power tolerance



Made In Italy Enginereed and produced in Italy



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Front STC* electrical characteristics

Pmpp** [W]	Efficiency [%]	lsc [A]	Voc [V]	Impp [A]	Vmpp [V]	FF
4,750	19,44	9,70	0,641	8,98	0,529	0,764
4,800	19,65	9,71	0,642	9,02	0,532	0,770
4,850	19,85	9,72	0,644	9,03	0,537	0,774
4,875	19,95	9,73	0,645	9,04	0,539	0,777
4,900	20,06	9,73	0,646	9,05	0,541	0,779
4,925	20,16	9,76	0,647	9,07	0,543	0,780
4,950	20,26	9,76	0,648	9,08	0,545	0,782
5,000	20,47	9,78	0,650	9,13	0,548	0,787
5,050	20,67	9,79	0,652	9,19	0,550	0,792

Most available Power classes

*STC (1000 W/m², AM 1,5 - 25°C) IEC 60904-3 Ed.2 ** High Reliability with guaranteed -0/+0,025 W positive power tollerance Measurement tolerances: ± 1.5 % rel. (P_{MPP}); ± 5 % rel. (I_{Sc} V_{oc})

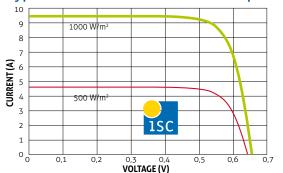
Typical 60 cells module's peak power generation with different cell-to-module (CTM) loss

19,44		285,0	282,2	279,3
19,65	_ N _	288,0	285,1	282,2
19,85		291,0	288,1	285,2
19,95		292,5	289,6	286,7
20,06		294,0	291,1	288,1
20,16		295,5	292,5	289,6
20,26		297,0	294,0	291,1
20,47		300,0	297,0	294,0
20,67		303,0	300,0	296,9
	19,65 19,85 19,95 20,06 20,16 20,26 20,47	19,65 19,85 19,95 20,06 20,16 20,26 20,47	19,65 288,0 19,85 291,0 19,95 292,5 20,06 294,0 20,16 295,5 20,26 297,0 20,47 300,0	19,65 288,0 285,1 19,85 291,0 288,1 19,95 292,5 289,6 20,06 294,0 291,1 20,16 295,5 292,5 20,26 297,0 294,0 20,47 300,0 297,0

Physical Characteristics

	Front	Back			
Product	Monocrystalline Silicon Cell using N type wafer				
Dimensions	156,75 x 156,75 +/- 0,5 mm				
Materials	Alkaline texturized surface				
	Blue & Light Blue silicon nitride AR coating				
Bus bar	Positive pole (+),	Negative pole (-),			
	four bus bar 1,00 +/- 0,1mm	four bus bar 1,00 +/- 0,1 mm			
	Distance axis: 39 mm	Distance axis: 39 mm			
Thickness (Si)	180 - 200 +/-20 μm				

Typical I-V curve at 4.950W front power cell

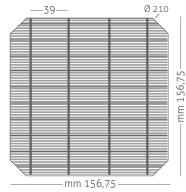


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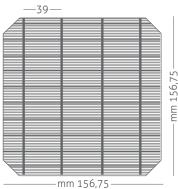
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Layout front



Layout rear



Temperature coefficients

• Current + 0.041 % / °C

• Voltage - 0.280 % / °C

• Power - 0.397 % / °C

Processing recommendation

Solder joint Copper ribbons coated with:

- 15 25 µm:
- 60 % Sn / 38 % Pb / 2 % Ag or 60 % Sn / 40 % Pb

Cells per bypass diode:

• Maximum 24 cells per bypass diode.

Storage remarks

Keep the cells at room temperature and in a dry and clean atmosphere (25°C ± 5°C).

